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EEPROM EPROM flash address polling most significant bit

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1 [The CAN microcluster: Parallel processing over the controller area network](#)



Paul A. Kuban, Rammohan K. Ragade

March 2005 **Journal on Educational Resources in Computing (JERIC)**, Volume 5 Issue 1

Publisher: ACM Press

Full text available:  pdf(242.37 KB) Additional Information: [full citation](#), [abstract](#), [references](#), [index terms](#)

Most electrical engineering and computer science undergraduate programs include at least one course on microcontrollers and assembly language programming. Some departments offer legacy courses in C programming, but few include C programming from an embedded systems perspective, where it is still regularly used. Distributed computing and parallel processing are subjects generally reserved for graduate programs or specialized degrees. And although it is common to provide undergraduate courses on c ...

Keywords: CAN, Cluster, controller area network, distributed, embedded systems, microcontrollers, parallel



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A 90-nm CMOS 1.8-V 2-Gb NAND flash memory for mass storage application

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Abstract

A 1.8-V 2-Gb NAND flash memory has been successfully developed on a 90-nm CMOS STI process technology, resulting in a 2/ die size and a 0.044-/spl mu/m/sup 2/ effective cell. For the higher level integration, critical layers are patterned with The device has three notable differences from previous generations. 1) The cells are organized in a single (16K+512) c array by adopting a one-sided row decoder in order to minimize the die size. 2) The bitline precharge level is set to 0.9 on-cell current. 3) During the program operations, the string select line, which connects the NAND cell strings to the bitline sub-V/sub CC/ in order to avoid program disturbance issues.

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Author Keywords

Not Available

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L1	22721220	@ad<"20020718"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/07/21 13:48
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L3	12	(Salvatore near2 Poli).in.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/07/21 13:51
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L7	8	(Antonino near2 Malfa).in.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/07/21 13:51
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L9	48036	nonvolatile adj memory	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/07/21 13:51

EAST Search History

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L12	35034	select\$4 adj memory	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/07/21 13:51
L13	121677	select\$4 near3 memory	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/07/21 13:51
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L33	3	1 and 31	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/07/21 13:56
L34	0	23 and 32	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/07/21 13:56
L35	0	23 and 33	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/07/21 13:56